

Chroma Amplifier Transistor (300V, 0.1A)

2SC4061K / 2SC3415S / 2SC4015 / 2SC3271F

●Features

- 1) High breakdown voltage. ($BV_{CEO}=300V$)
- 2) Low collector output capacitance, typically 3pF at $V_{CB}=30V$.
- 3) Ideal for chroma circuit.

●Packaging specifications and hFE

Type	2SC4061K	2SC3415S	2SC4015	2SC3271F
Package	SMT3	SPT	ATV	TO-126F
hFE	NP	NP	N	N
Marking	AN*	—	—	—
Code	T146	TP	TV2	—
Basic ordering unit (pieces)	3000	5000	2500	1000

* Denotes hFE

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	300	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	300	—	—	V	$I_C=100\mu A$
Emitter-base breakdown voltage	BV_{EBO}	5	—	—	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	—	—	0.5	μA	$V_{CB}=200V$
Emitter cutoff current	I_{EBO}	—	—	0.5	μA	$V_{EB}=4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	2	V	$I_C/I_E=50mA/5mA$
DC current transfer ratio	hFE	56	—	180	—	$V_{CE}/I_C=10V/10mA$
Gain bandwidth product	fT	50	100	—	MHz	$V_{CE}=30V, I_E=-10mA, f=100MHz$
Collector output capacitance	Cob	—	3	—	pF	$V_{CB}=30V, I_E=0A, f=1MHz$

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	300	V
Collector-emitter voltage	V_{CEO}	300	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector power dissipation	2SC4061K	0.2	W (Tc=25°C)
	2SC3415S	0.3	
	2SC4015	1	
	2SC3271F	5	
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55~+150	°C

* When l = 1.7mm and the foil collector area on the PC board is 100mm² or greater.

(96-172-C52)

High-voltage Switching Transistor (400V, 5A)

2SC4938 / 2SC4129

●Features

- 1) Low saturation voltage, typically $V_{CE(sat)}=0.6V$ at $I_C/I_E=5A/1A$.
- 2) High switching speed, typically $t_f=1\mu s$ at $I_C=4A$.
- 3) Wide SOA (safe operating area).

●Packaging specifications and hFE

Type	2SC4938	2SC4129
Package	PSD3	TO-220FP
hFE	B	AB
Code	TL	—
Basic ordering unit (pieces)	1000	500

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	V_{CBO}	400	V
Collector-emitter voltage	V_{CEO}	400	V
Emitter-base voltage	V_{EBO}	7	V
Collector current	I_C	5	A
	I_{CP}	7	A *
Collector power dissipation	2SC4938	1.5	W (Tc=25°C)
	2SC4129	35	
	2SC4129	30	
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55~+150	°C

* Single pulse, Pw=100ms.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	BV_{CBO}	400	—	—	V	$I_C=50\mu A$
Collector-emitter breakdown voltage	BV_{CEO}	400	—	—	V	$I_C=1mA$
Emitter-base breakdown voltage	BV_{EBO}	7	—	—	V	$I_E=50\mu A$
Collector cutoff current	I_{CBO}	—	—	10	μA	$V_{CB}=400V$
Emitter cutoff current	I_{EBO}	—	—	10	μA	$V_{EB}=5V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	—	—	1	V	$I_C/I_E=5A/1A$ *
Base-emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	$I_C/I_E=5A/1A$ *
DC current transfer ratio	2SC4938	25	—	50	—	$V_{CE}/I_C=5V/2A$
	2SC4129	16	—	50	—	
Transition frequency	fT	—	15	—	MHz	$V_{CB}=10V, I_E=-0.5A, f=5MHz$ *
Output capacitance	Cob	—	80	—	pF	$V_{CB}=10V, I_E=0A, f=1MHz$
Turn-on time	t _{on}	—	—	1	μs	$I_C=4A, R_L=50\Omega$
Storage time	t _{stg}	—	—	2.5	μs	$I_{B1}=-I_{B2}=0.4A$
Fall time	t _f	—	—	1	μs	$V_{CC}\approx 200V$

* Measured using pulse current.

(96-188-C55)